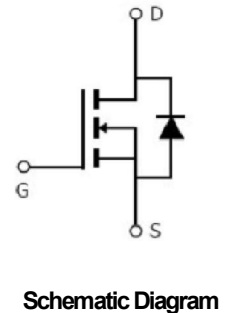
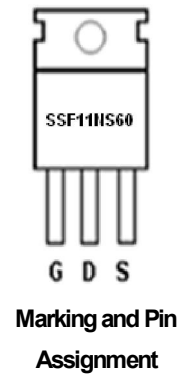
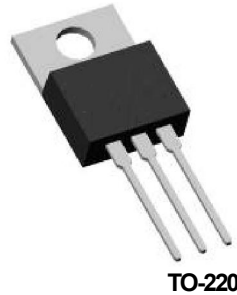


Main Product Characteristics

V_{DS}	600V
$R_{DS(on)}$	0.36 Ω (typ.)
I_D	11A



Features and Benefits

- High dv/dt and avalanche capabilities
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Lead free product



Description

The SSF11NS60 series MOSFET is a new technology, which combines an innovative super junction technology and advance process. This new technology achieves low $R_{DS(on)}$, energy saving, high reliability and uniformity, superior power density and space saving.

Absolute Max Rating

Symbol	Parameter	Max.	Units
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V ^①	11	A
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V ^①	7	
I_{DM}	Pulsed Drain Current ^②	44	
P_D @ TC = 25°C	Power Dissipation ^③	162	W
	Linear Derating Factor	1.5	W/°C
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy @ L=22.5mH	281	mJ
I_{AS}	Avalanche Current @ L=22.5mH	5	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

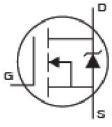
Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ^③	—	0.77	°C/W
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10s$) ^④	—	62	°C/W

Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	600	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	0.36	0.41	Ω	$V_{GS}=10V, I_D = 5.5A$
		—	0.88	—		$T_J = 125^\circ\text{C}$
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
		—	2.46	—		$T_J = 125^\circ\text{C}$
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 600V, V_{GS} = 0V$
		—	—	50		$T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 30V$
		—	—	-100		$V_{GS} = -30V$
Q_g	Total gate charge	—	28.41	—	nC	$I_D = 11A,$ $V_{DS}=480V,$ $V_{GS} = 10V$
Q_{gs}	Gate-to-Source charge	—	6.64	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	12.34	—		
$t_{d(on)}$	Turn-on delay time	—	12.85	—	ns	$V_{GS}=10V, V_{DS}=300V,$ $R_L=54.5\Omega,$ $R_{GEN}=4.7\Omega$ $I_D=5.5A$
t_r	Rise time	—	9.45	—		
$t_{d(off)}$	Turn-Off delay time	—	30.40	—		
t_f	Fall time	—	6.30	—		
C_{iss}	Input capacitance	—	824.8	—	pF	$V_{GS} = 0V$
C_{oss}	Output capacitance	—	78.06	—		$V_{DS} = 50V$
C_{rss}	Reverse transfer capacitance	—	2.75	—		$f = 600\text{KHz}$

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	11	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	44	A	
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$I_S=11A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	—	313	—	ns	$T_J = 25^\circ\text{C}, I_F = 11A, di/dt = 100A/\mu s$
Q_{rr}	Reverse Recovery Charge	—	2.97	—	uC	



EAS test circuits:



- ① The maximum current rating is limited by bond-wires.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$
- ⑤ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})} = 150^\circ\text{C}$.

Typical Electrical and Thermal Characteristics

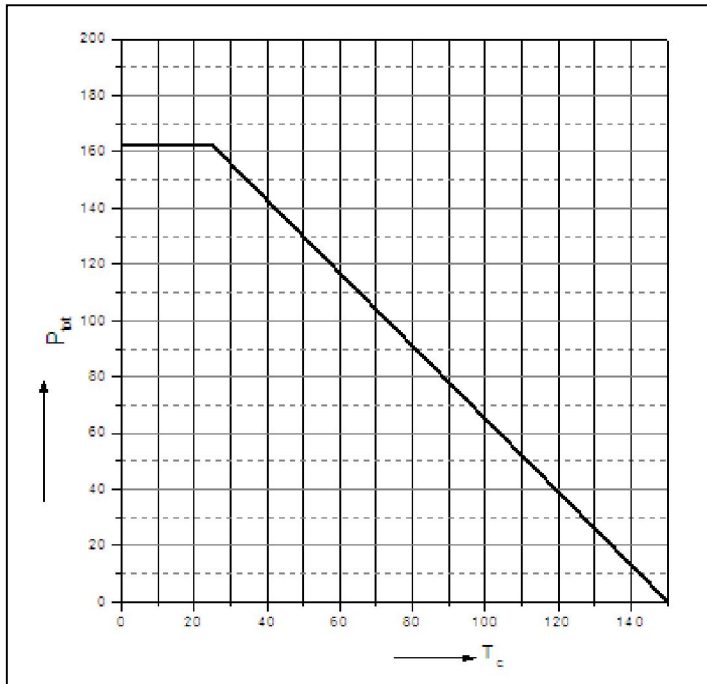


Figure 1: Power dissipation

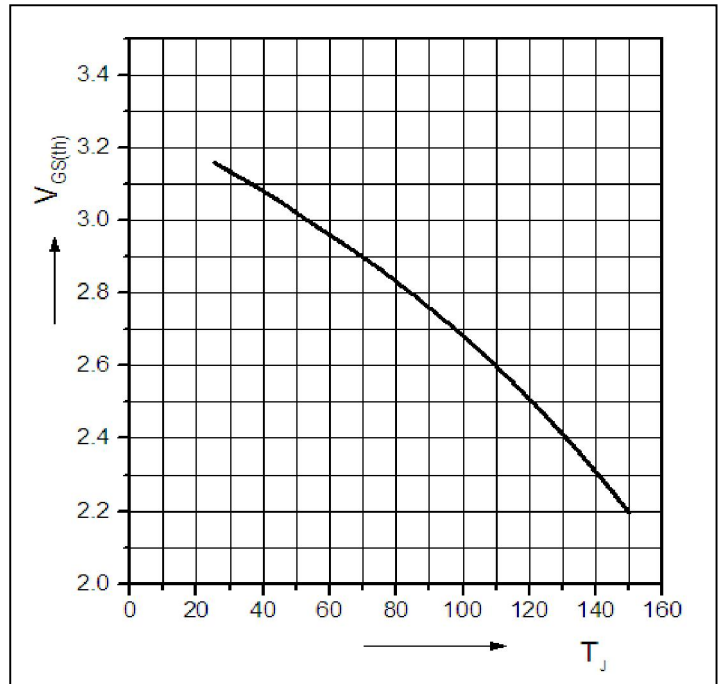


Figure 2: Typ. Gate to source cut-off voltage

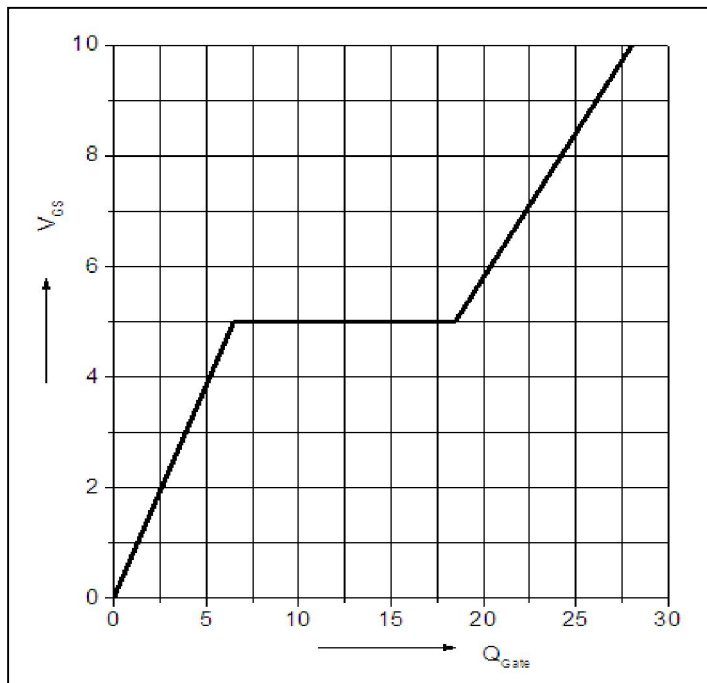


Figure 3: Typ. gate charge

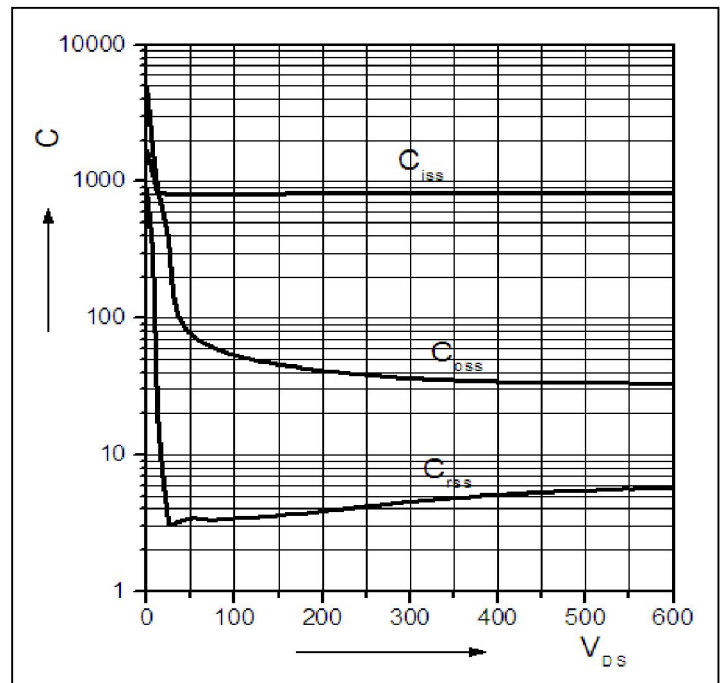


Figure 4: Typ. Capacitances

Typical Electrical and Thermal Characteristics

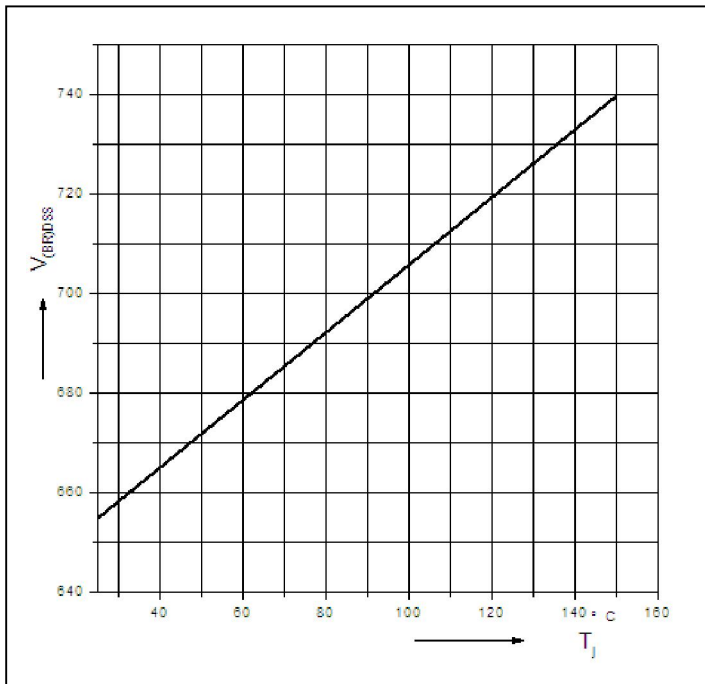


Figure 5. Drain-source breakdown voltage

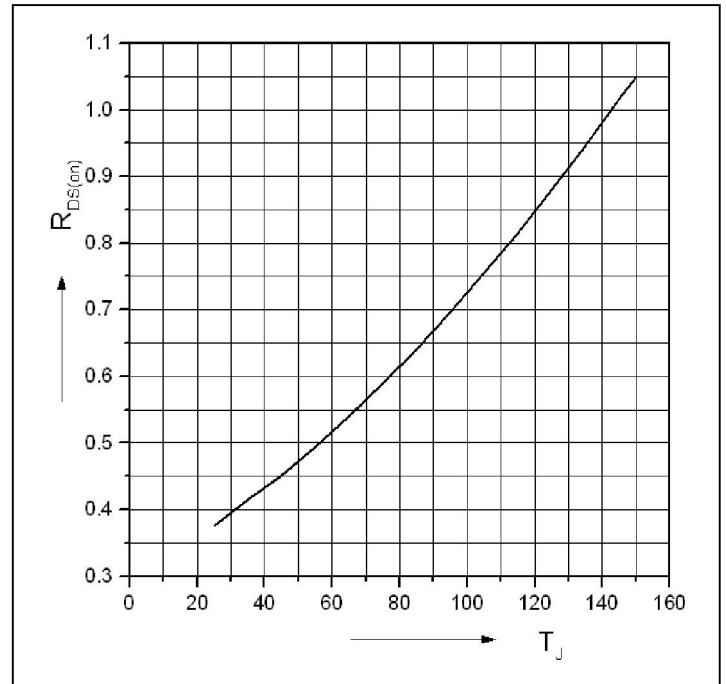
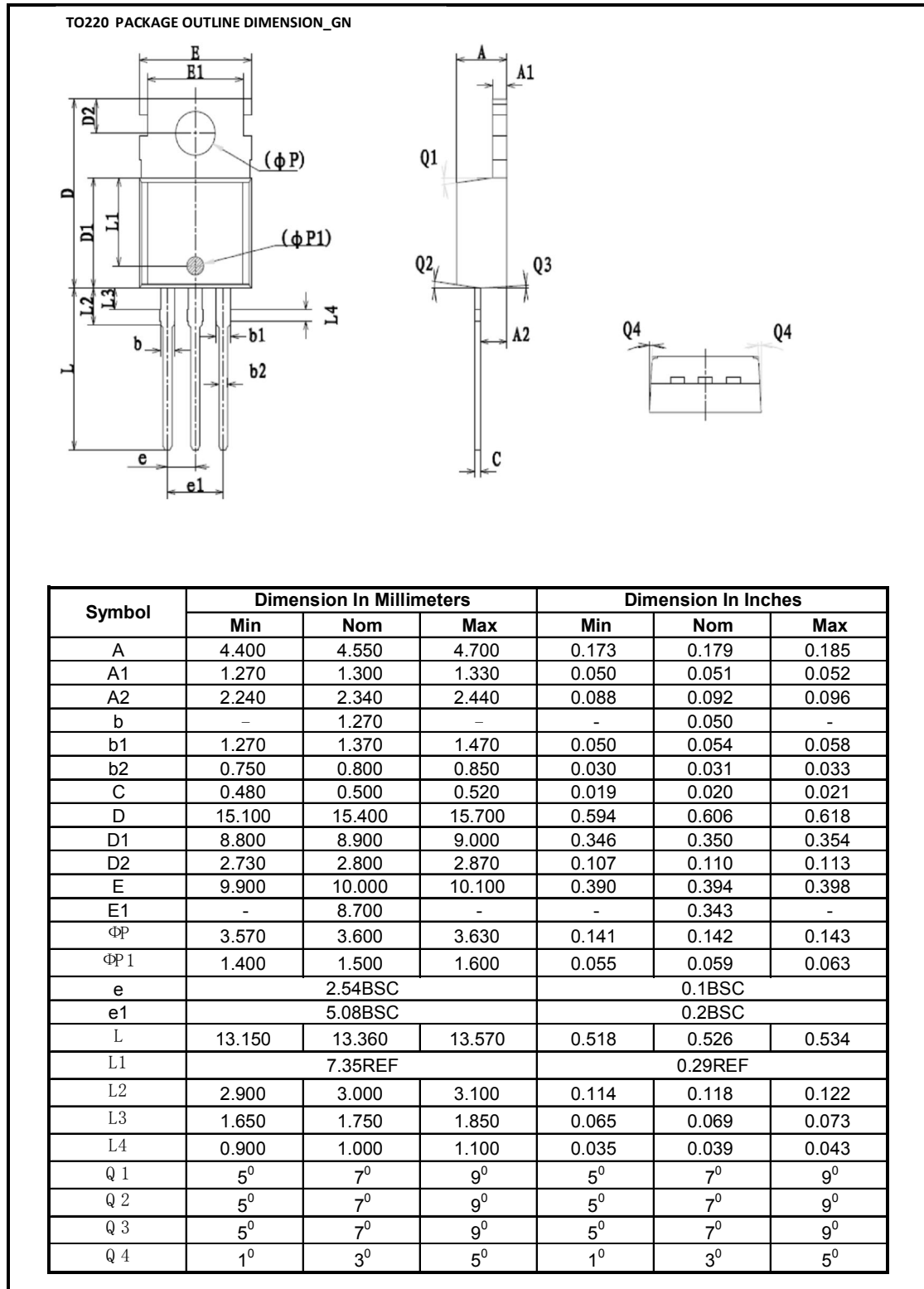


Figure 6. Drain-source on-state resistance

Mechanical Data



Ordering and Marking Information

Device Marking: SSF11NS60

Package (Available)

TO220

Operating Temperature Range

C : -55 to 150 °C

Devices per Unit

Package Type	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO220	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	$T_j=125^{\circ}\text{C}$ to 150°C @ 80% of Max $V_{DSS}/V_{CES}/V_R$	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	$T_j=150^{\circ}\text{C}$ @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices